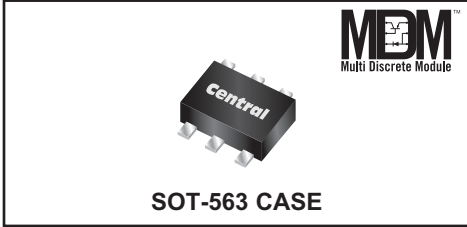


**CMLM0405**  
**MULTI DISCRETE MODULE™**  
 SURFACE MOUNT SILICON  
 LOW  $V_{CE(SAT)}$  NPN TRANSISTOR AND  
 LOW  $V_F$  SCHOTTKY DIODE



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLM0405 is a single NPN transistor and Schottky diode packaged in a space saving SOT-563 case and designed for small signal general purpose applications where size and operational efficiency are prime requirements.

- Complementary Device: **CMLM0605**
- Combination Low  $V_{CE(SAT)}$  Transistor and Low  $V_F$  Schottky Diode.

**MARKING CODE: C45**

**MAXIMUM RATINGS - CASE: ( $T_A=25^\circ\text{C}$ )**

Power Dissipation  
 Operating and Storage Junction Temperature  
 Thermal Resistance

SYMBOL		UNITS
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	357	$^\circ\text{C/W}$

**MAXIMUM RATINGS - Q1: ( $T_A=25^\circ\text{C}$ )**

Collector-Base Voltage  
 Collector-Emitter Voltage  
 Emitter-Base Voltage  
 Continuous Collector Current

SYMBOL		UNITS
$V_{CBO}$	60	V
$V_{CEO}$	40	V
$V_{EBO}$	6.0	V
$I_C$	200	mA

**MAXIMUM RATINGS - D1: ( $T_A=25^\circ\text{C}$ )**

Peak Repetitive Reverse Voltage  
 Continuous Forward Current  
 Peak Repetitive Forward Current,  $t_p \leq 1.0\text{ms}$   
 Peak Forward Surge Current,  $t_p = 8.0\text{ms}$

SYMBOL		UNITS
$V_{RRM}$	40	V
$I_F$	500	mA
$I_{FRM}$	3.5	A
$I_{FSM}$	10	A

**ELECTRICAL CHARACTERISTICS - Q1: ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{CEV}$	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$			50	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	60	120		V
$BV_{CEO}$	$I_C=1.0\text{mA}$	40	60		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0	7.5		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.057	0.100	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.090	0.200	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.65	0.75	0.85	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.85	0.95	V
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$	90	180		
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	100	185		
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100	180	300	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	70	150		
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	30	90		
$f_T$	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz
$C_{ob}$	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$			4.0	pF
$C_{ib}$	$V_{BE}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$			8.0	pF
$h_{ie}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$		1.0	12	k $\Omega$
$h_{re}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$		0.1	10	$\times 10^{-4}$

R5 (8-January 2018)

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**LOW  $V_F$  SCHOTTKY DIODE**



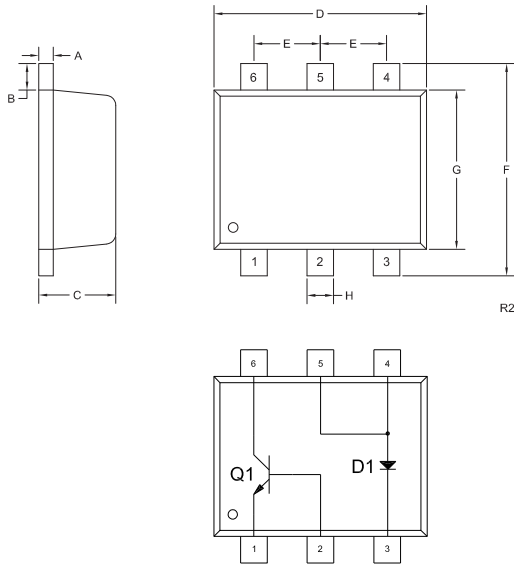
**ELECTRICAL CHARACTERISTICS - Q1 - Continued:**

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$h_{fe}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	100	400	
$h_{oe}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0	60	$\mu S$
NF	$V_{CE}=5.0V, I_C=100\mu A, R_S=1.0K\Omega,$ $f=10Hz$ to $15.7kHz$		4.0	dB
$t_d$	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_{B1}=1.0mA$		35	ns
$t_r$	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_{B1}=1.0mA$		35	ns
$t_s$	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$		200	ns
$t_f$	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$		50	ns

**ELECTRICAL CHARACTERISTICS - D1: ( $T_A=25^\circ C$ )**

$I_R$	$V_R=10V$		30	$\mu A$
$I_R$	$V_R=30V$		100	$\mu A$
$BV_R$	$I_R=500\mu A$	40		V
$V_F$	$I_F=100\mu A$		0.13	V
$V_F$	$I_F=1.0mA$		0.21	V
$V_F$	$I_F=10mA$		0.27	V
$V_F$	$I_F=100mA$		0.35	V
$V_F$	$I_F=500mA$		0.47	V
$C_J$	$V_R=1.0V, f=1.0MHz$		50	pF

**SOT-563 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS		MILLIMETERS	
	INCHES		MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R2)

**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Cathode D1
- 4) Anode D1
- 5) Anode D1
- 6) Collector Q1

**MARKING CODE: C45**

R5 (8-January 2018)

## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

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